

### REMARKS

The status of the application is as follows. Claims 1-7 were presented for prosecution and stand finally rejected. Namely, claims 1-7 were rejected under 35 USC 102(b) as being anticipated by Saran et al. (EP 0875934A2), and claim 2 was rejected under 35 USC 103(a) as being obvious over Saran in view of Zavracky et al. Claim 1 has been amended herein. Support for the amendment is found in the last paragraph on page 3, and is shown in Figure 2. No new matter is believed added.

With respect to claim 2, the Examiner states that Saran fails to disclose "via lines of tungsten." However, claim 2 was also rejected under 102(a) as being anticipated by Saran. Clarification of the rejection(s) is respectfully requested.

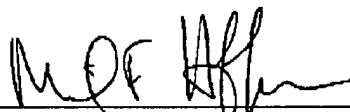
Applicants respectfully submit that claim 1 and its dependent claims are not anticipated by Saran. As amended, claim 1 recites "... a bond pad disposed above at least one layered structure, wherein the layered structure comprises a metal layer and a layer of dielectric material, characterized in that via lines are present in the layer of a dielectric material, which via lines are connected to the metal layer to form isolated areas filled with dielectric material." Accordingly, the present invention provides, *inter alia*, via lines that "are connected to the metal layer."

Conversely, Saran only teaches reinforcing metalization lines that **do not** extend and connect to a metal layer. This is clearly depicted in Figures 1, 3 and 5 of Saran, where it can be seen that the metalization extends upwardly into, and is capped off by three layers of dielectric material 32, 34 and 36. Moreover, there is no teaching in Saran of reinforcing via lines that connect to a metal layer. Accordingly, because Saran fails to

teach each and every feature of claim 1, Applicants respectfully submit that claim 1, and the claims that depend therefrom are in condition for allowance.

In light of the above, Applicants submit that all claims are in condition for allowance. If the Examiner believes that anything further is necessary to place the application in condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney at the telephone number listed below.

Respectfully submitted,



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Dated: November 7, 2002

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**SEPARATE MARKUP SHEET****In the Claims**

1. (AMENDED) A semiconductor device comprising a bond pad structure, which bond pad structure comprises a bond pad disposed above at least one layered structure, wherein the layered structure comprises a metal layer and a layer of dielectric material, characterized in that via lines are present in the layer of a dielectric material, which via lines are [arranged in such a way that] connected to the metal [layers] layer to [and the via lines] form [all] isolated areas filled with dielectric material.

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